

R-C Thermal Model Parameters

DESCRIPTION

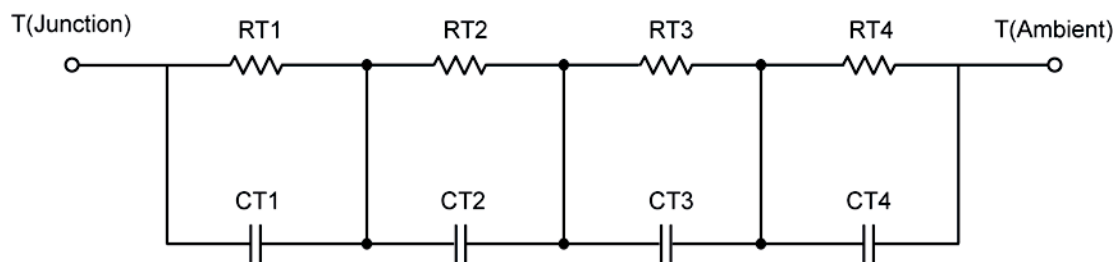
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

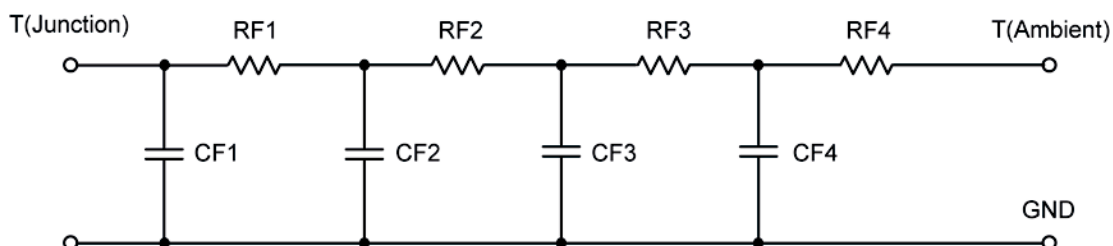
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	6.4662	N/A	12.0883
RT2	20.1880	N/A	10.3992
RT3	26.5059	N/A	11.2277
RT4	56.9154	N/A	1.2848
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	4.1930 m	N/A	183.8612 m
CT2	113.5926 m	N/A	6.1898 m
CT3	17.3701 m	N/A	33.4172 m
CT4	1.6390	N/A	1.1851 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)			
Junction to	Ambient	Case	Foot
RF1	11.3834	N/A	4.9418
RF2	30.0190	N/A	12.0522
RF3	15.4111	N/A	12.2565
RF4	53.1865	N/A	5.7495
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)			
Junction to	Ambient	Case	Foot
CF1	3.4497 m	N/A	2.2530 m
CF2	13.8546 m	N/A	4.2653 m
CF3	143.9691 m	N/A	36.5119 m
CF4	1.5561	N/A	332.2691 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

